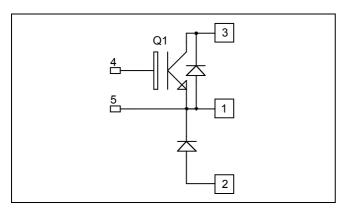
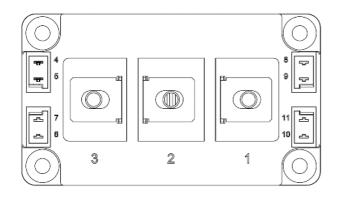


Buck Chopper NPT IGBT Power Module





$V_{CES} = 600V$ $I_{C} = 330A$ @ Tc = 80°C

Application

- AC and DC motor control
- Switched Mode Power Supplies

Features

- Non Punch Through (NPT) FAST IGBT
 - Low voltage drop
 - Low tail current
 - Switching frequency up to 50 kHz
 - Soft recovery parallel diodes
 - Low diode VF
 - Low leakage current
 - RBSOA and SCSOA rated
- Kelvin emitter for easy drive
- High level of integration
- M6 power connectors

Benefits

- Stable temperature behavior
- Very rugged
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive T_C of V_{CEsat}
- RoHS Compliant

Absolute maximum ratings

Symbol	Parameter		Max ratings	Unit	
V _{CES}	Collector - Emitter Breakdown Voltage		600	V	
I _C	Continuous Collector Current	$T_C = 25^{\circ}C$	520		
	Continuous Conector Current	$T_C = 80^{\circ}C$	330	А	
I _{CM}	Pulsed Collector Current	$T_C = 25^{\circ}C$	800		
V _{GE}	Gate – Emitter Voltage		±20	V	
P _D	Maximum Power Dissipation	$T_C = 25^{\circ}C$	1560	W	
RBSOA	Reverse Bias Safe Operating Area	$T_j = 125^{\circ}C$	800A @ 520V		

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com APTGF330SK60D3G-Rev 2 October 2012

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All ratings @ $T_j = 25^{\circ}C$ unless otherwise specified

Electrical Characteristics Symbol Characteristic **Test Conditions** Min Тур Max Unit Zero Gate Voltage Collector Current $V_{GE} = 0V, V_{CE} = 600V$ 500 μΑ ICES $V_{GE} = 15V$ $T_i = 25^{\circ}C$ 1.95 2.45 V Collector Emitter saturation Voltage V_{CE(sat)} $I_{\rm C} = 400 {\rm A}$ $T_i = 125^{\circ}C$ 2.2 $V_{GE} = V_{CE}, I_C = 7.5 \text{ mA}$ 5.0 5.8 V V_{GE(th)} Gate Threshold Voltage 6.5 $V_{GE} = 20V, V_{CE} = 0V$ Gate - Emitter Leakage Current 1200 nA IGES

Dynamic Characteristics

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
Cies	Input Capacitance	$V_{GE} = 0V; V_{CE} = 25V$ f = 1MHz			18		nF
C _{res}	Reverse Transfer Capacitance				1.6		m
Q _G	Gate charge	V_{GE} =15V, I _C =40 V _{CE} =300V		1.3		μC	
T _{d(on)}	Turn-on Delay Time	Inductive Switching (25°C)			150		
Tr	Rise Time	$V_{GE} = \pm 15V$			72		
T _{d(off)}	Turn-off Delay Time	$V_{Bus} = 300V$ $I_{C} = 400A$ $R_{G} = 8\Omega$			530		ns
$T_{\rm f}$	Fall Time				40		
T _{d(on)}	Turn-on Delay Time	Inductive Switching (125°C) $V_{GE} = \pm 15V$ $V_{Bus} = 300V$ $I_C = 400A$ $R_G = 8\Omega$			160		ns
Tr	Rise Time				75		
T _{d(off)}	Turn-off Delay Time				550		
T _f	Fall Time				50		
Eon	Turn on Energy	$V_{GE} = \pm 15V$ $V_{Bus} = 300V$	$T_j = 125^{\circ}C$		18		mJ
E _{off}	Turn off Energy	$I_{\rm C} = 400 {\rm A}$ $R_{\rm G} = 8 {\rm \Omega}$	$T_j = 125^{\circ}C$		17		1115
I _{sc}	Short Circuit data	$V_{GE} \le 15V$; $V_{Bus} = 360V$ $t_p \le 10\mu s$; $T_1 = 125^{\circ}C$			1800		А

Reverse diode ratings and characteristics

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
V _{RRM}	Maximum Peak Repetitive Reverse Voltage			600			V
I _{RRM}	Maximum Reverse Leakage Current	$V_R = 600V$	$T_i = 25^{\circ}C$ $T_i = 125^{\circ}C$			750 1000	μΑ
I _F	DC Forward Current		$Tc = 80^{\circ}C$		400		Α
$V_{\rm F}$	Diode Forward Voltage	$I_{\rm F} = 400 {\rm A}$ $V_{\rm GE} = 0 {\rm V}$	$T_i = 25^{\circ}C$		1.25	1.6	v
		$V_{GE} = 0V$	$T_{i} = 125^{\circ}C$		1.2		
t _{rr}	Reverse Recovery Time		$T_j = 25^{\circ}C$		150	ns	
ι _{rr}	Reverse Recovery Time	I = 400 A	$T_{j} = 125^{\circ}C$		250		115
Q _{rr}	Reverse Recovery Charge	$I_{\rm F} = 400 {\rm A}$ $V_{\rm R} = 300 {\rm V}$	$T_j = 25^{\circ}C$		27		шС
Qrr	Reverse Recovery Charge	$v_{\rm R} = 300 v$ di/dt =4400A/µs	$T_{j} = 125^{\circ}C$		44		μC
E _{rr}	Reverse Recovery Energy		$T_j = 25^{\circ}C$		5.6		mJ
	Reverse Recovery Energy		$T_{i} = 125^{\circ}C$		9.2		1113

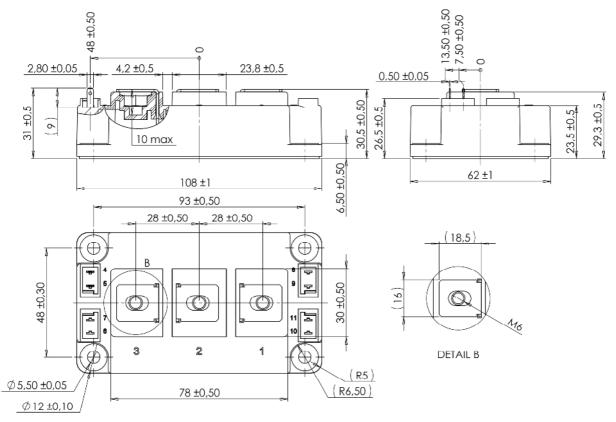
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Thermal and package characteristics

Symbol	Characteristic			Min	Тур	Max	Unit
R _{thJC}	Junction to Case Thermal Resistance		IGBT			0.08	°C/W
	sufficient to case Therman Resistance		Diode			0.15	C/ W
V _{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz			4000			V
T _J	Derating junction temperature range -40 150				150		
T _{STG}	Storage Temperature Range			-40		125	°C
T _C	Operating Case Temperature			-40		125	
Torque	Mounting torque	For terminals	M6	3		5	N.m
	Mounting torque	To Heatsink	M6	3		5	
Wt	Package Weight					350	g

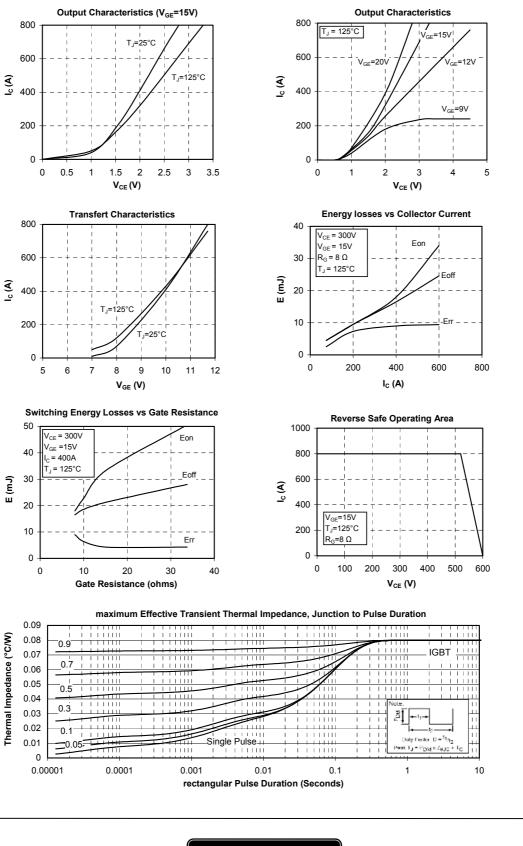
D3 Package outline (dimensions in mm)



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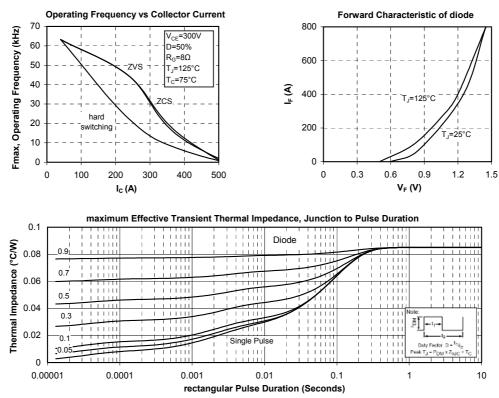
Typical Performance Curve



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